

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

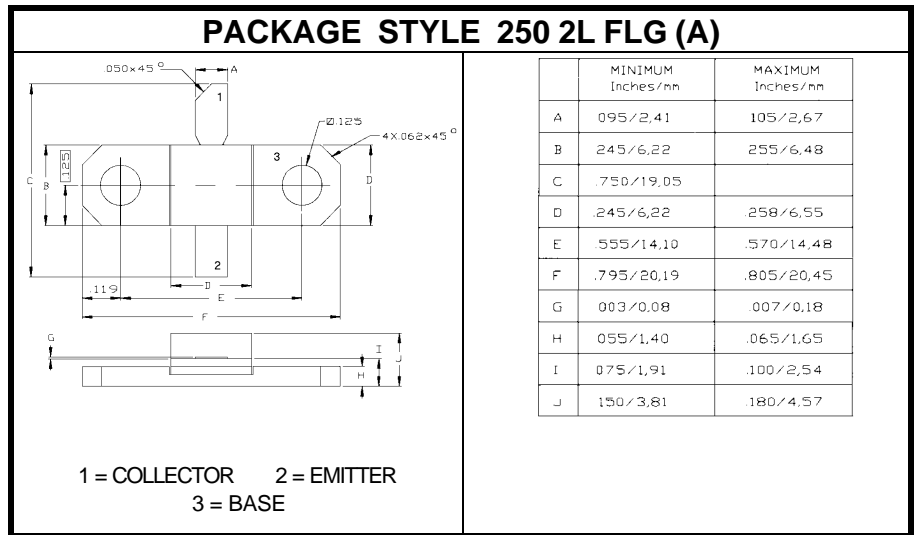
The **ASI SD1530-7** is a Common Base Device Designed for DME, IFF and Tacan Pulse Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Broad Band Performance

MAXIMUM RATINGS

I_C	2.5 A
V_{CES}	55 V
P_{DISS}	125 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	1.4 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I _C = 75 mA	55			V
BV_{EBO}	I _E = 25 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 300 mA	10			---
P_G h_c	V _{CC} = 50 V P _{out} = 25 W PULSE WIDTH = 10 μS	8.5	10 45		dB %
	fo = 960 to 1215 MHz DUTY CYCLE = 1.0%				